



## TO-92 Plastic-Encapsulate Transistors

### **MPSA56** TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM}: \quad 0.625 \quad W \quad (T_{amb}=25^{\circ}C)$$

Collector current

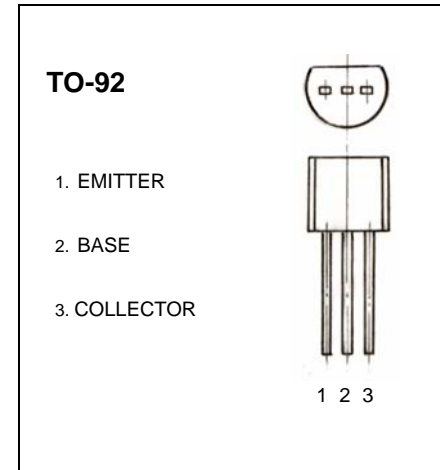
$$I_{CM}: \quad -0.5 \quad A$$

Collector-base voltage

$$V_{(BR)CBO}: \quad -80 \quad V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$



#### **ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-4			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-80V, I_E=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-100mA$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-1V, I_C=-100mA, f=100MHz$	50			MHz

# Typical Characteristics

# MPSA56

